

No.2111B

2SD1800

NPN Epitaxial Planar Silicon Transistor

Driver Applications

Applications

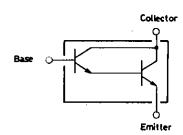
. Relay drivers, hammer drivers, lamp drivers, motor drivers

Features

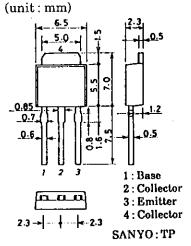
- High DC current gain (hFE≥ 4000)
- · Large current capacity
- Small and slim package making it easy to make 2SD1800-applied sets smaller

Absolute Maximum Ratings at Ta = 25°C			unit			
Collector to Base Voltage	V_{CBO}			80	V	
Collector to Emitter Voltage	V_{CEO}			50	V	
Emitter to Base Voltage	V_{EBO}			10	V	
Collector Current	$I_{\mathbf{C}}$			1.5	Α	
Collector Current(Pulse)	I_{CP}			3	Α	
Collector Dissipation	P_{C}			1	W	
-	_	$T_c = 25^{\circ}C$		10	W	
Junction Temperature	${f Tj}$			150	°C	
Storage Temperature	Tstg		-55 to $+$	150	°C	
Electrical Characteristics at Ta = 25°C			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 40V, I_E = 0$,,	100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 8V, I_C = 0$			100	nА
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 2V_1I_C = 500 \text{mA}$	4000			
	$h_{FE}(2)$	$V_{CE} = 2V_{AC} = 10 \text{ mA}$	3000			
Gain-Bandwidth Product	$\mathbf{f_T}^-$	$V_{CE} = 10V, I_{C} = 50mA$		120		MHz
C-E Saturation Voltage	$V_{\mathrm{CE}(\mathrm{sat})}$	$I_C = 500 \text{mA}, I_B = 0.5 \text{mA}$		0.9	1.5	V
B-E Saturation Voltage	$V_{\mathrm{BE(sat)}}$	$I_C = 500 \text{mA}, I_B = 0.5 \text{mA}$		1.5	2.0	v
C-B Breakdown Voltage	$V_{(BR)CBO}$		80			V
C-E Breakdown Voltage	V _{(BR)CEO}		50			V
E-B Breakdown Voltage	V _{(BR)EBO}		10			v

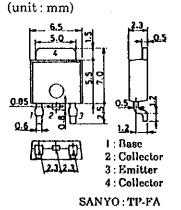
Electrical Connection

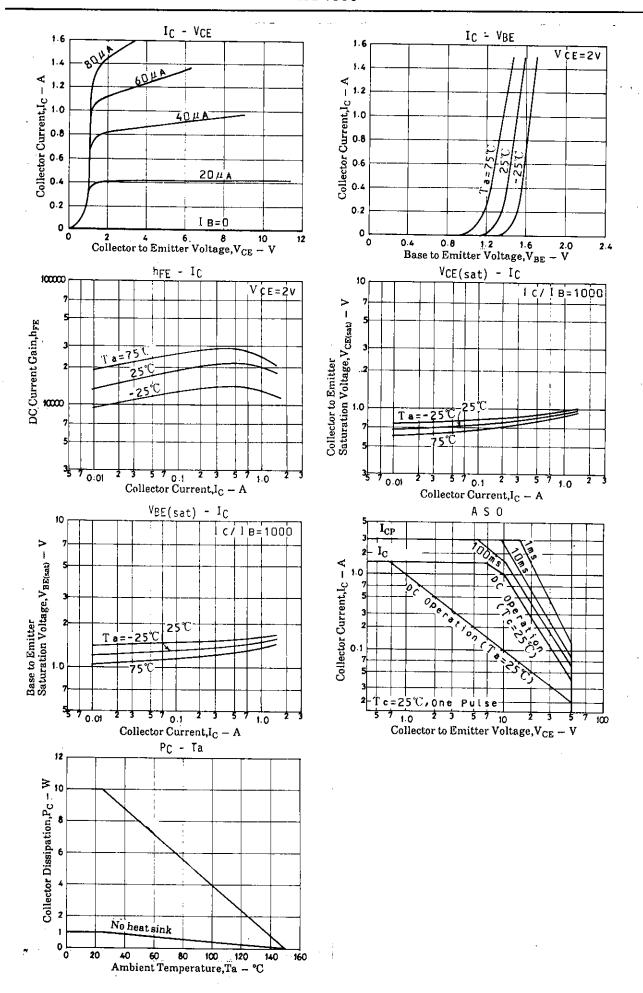


Package Dimensions 2045B



Package Dimensions 2044B





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